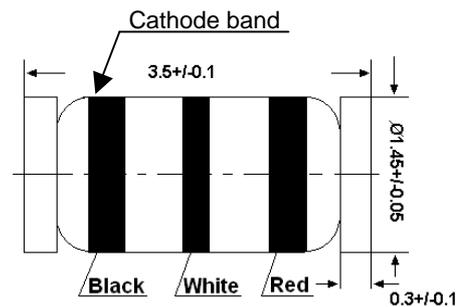


LL914...LL4454

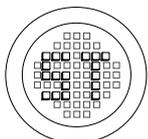
SILICON EPITAXIAL PLANAR DIODES for General Purpose and Switching.

LL-34



**Glass case MiniMELF
Dimensions in mm**

Type	Peak reverse voltage V_{RM} V	Max. aver. rectified current I_O mA	Max. power dissip. at 25°C P_{tot} mW	Max. junction temperature T_j °C	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
					V_F V	at I_F mA	I_n nA	at V_R V	t_{rr} ns	Conditions
LL914	100	75	500	200	1.0	10	25	20	max.4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4149	100	150	500	200	1.0	10	25	20	max.4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4151	75	150	500	200	1.0	50	50	50	max.2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4152	40	150	400	175	0.55	0.10	50	30	max.2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4153	75	150	400	175	0.55	0.10	50	50	max.2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4154	35	150	500	200	1.0	30	100	25	max.2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4447	100	150	500	200	1.0	20	25	20	max.4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4449	100	150	500	200	1.0	30	25	20	max.4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100\Omega$, to $I_R = 1$ mA
LL4450	40	150	400	175	0.54	0.50	50	30	max.4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
LL4451	40	150	400	175	0.50	0.10	50	30	max.10	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
LL4453	30	150	400	175	0.55	0.01	50	20	-	-
LL4454	75	150	400	175	1.0	10	100	50	max.4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA



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